Electronic Supplementary Material (ESI) for Physical Chemistry Chemical Physics.

Growth and ferroelectric domains of Diisopropylammonium Bromide films with 12-crown-4 addition at room temperature

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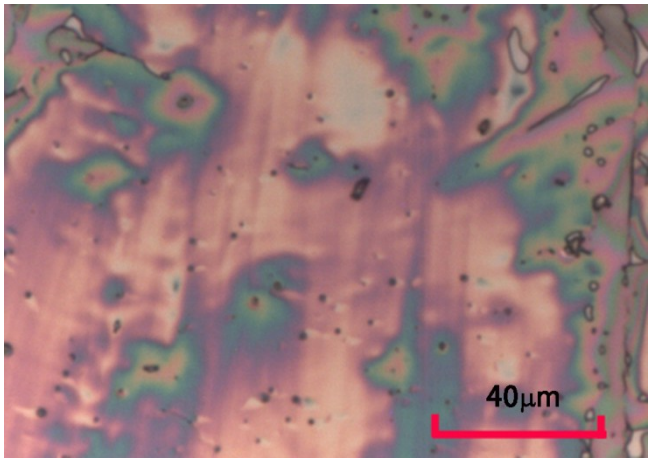


Fig. S1 Optical morphology of the $P2_12_12_1$ phase DIPAB films fabricated by spin-coating method at room temperature.

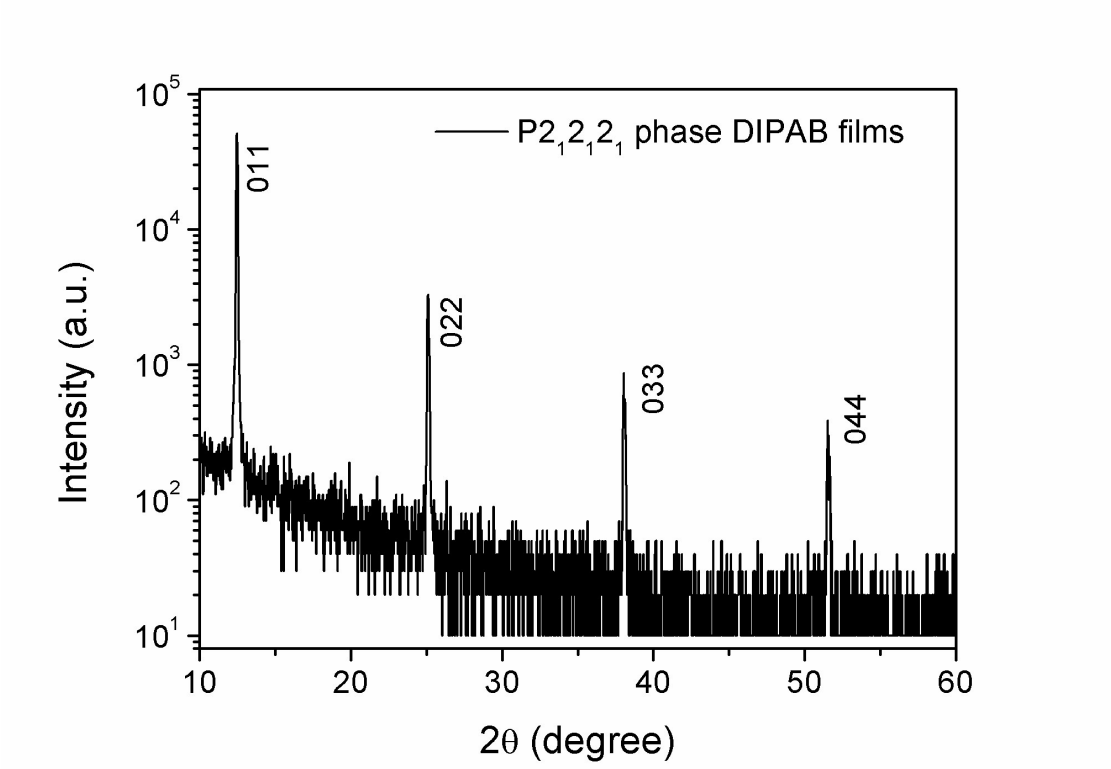
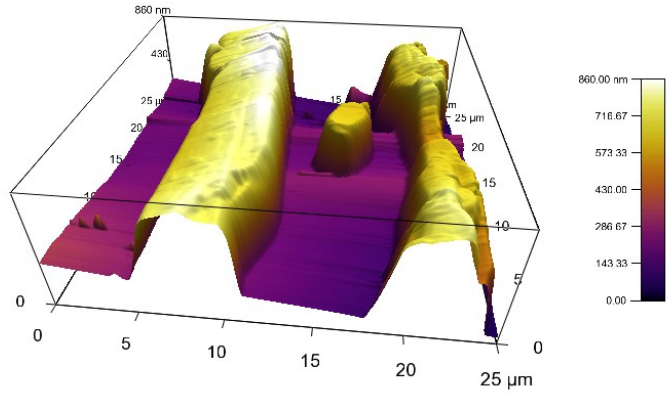


Fig. S2 XRD pattern of the $P2_12_12_1$ phase DIPAB films fabricated by spin-coating method at room temperature.



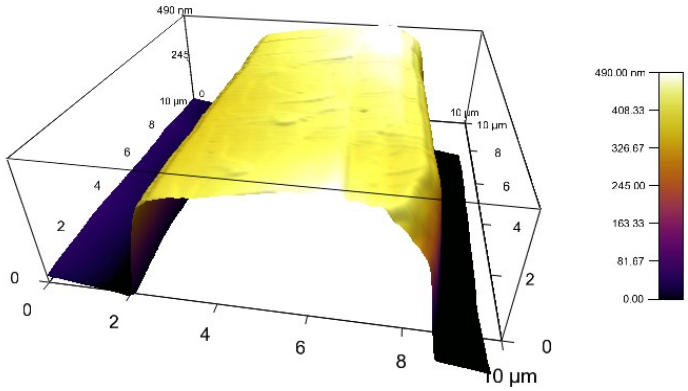


Fig. S3 Surface topography of the DIPAB thin films with a thickness of hundreds of nanometers on the Si substrates.

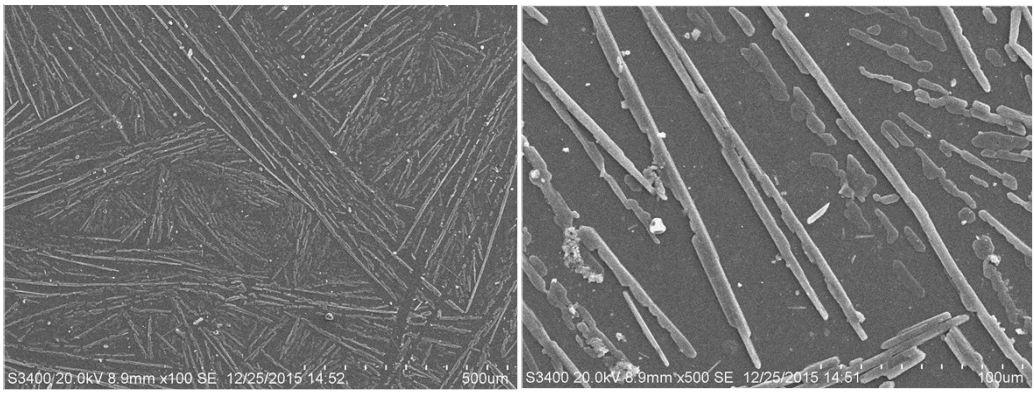


Fig. S4 SEM surface topography of the DIPAB thin films.